

Title (en)

Mask repair system.

Title (de)

Korrekturverfahren für Maske.

Title (fr)

Système de réparation des masques.

Publication

EP 0334680 A2 19890927 (EN)

Application

EP 89303016 A 19890328

Priority

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- JP 6975988 A 19880325

Abstract (en)

A method and apparatus for inspecting and repairing a mask usable in manufacture of semiconductor microcircuits, by using an electron beam is disclosed. The inspection and repair of a mask pattern are made in a single apparatus, by using a controlled current of electron beam. For inspection, the surface of a mask (4) having a mask pattern (3) and a radiation-sensitive layer (5), covering it, is scanned with an electron beam (6) and, by detecting (7) secondary electrons or reflected electrons caused at that time, the state of the pattern is inspected. If any defect is detected (12-15), the portion of the radiation-sensitive layer on the detected defect is irradiated with an electron beam of greater magnitude than that for the inspection and, thereafter, the exposed portion of the radiation-sensitive layer is removed. Then, etching or plating is made to the thus uncovered portion, whereby repair of the mask pattern is made.

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IPC 8 full level

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Cited by

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